

### **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

## IPW65R041CFD

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### FEATURES

- Static drain-source on-resistance: RDs(on)≤41mΩ
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

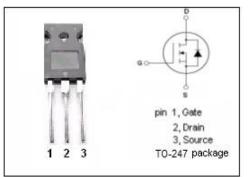
Fast Switching

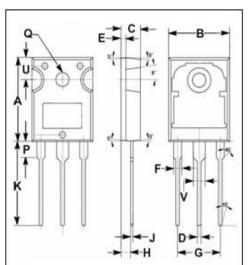
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

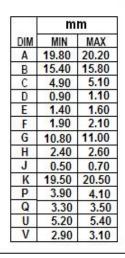
SYMBOL	PARAMETER	VALUE	UNIT			
V <sub>DSS</sub>	Drain-Source Voltage	650	V			
V <sub>GS</sub>	Gate-Source Voltage ±20		V			
ID	Drain Current-Continuous	68.5	A			
I <sub>DM</sub>	Drain Current-Single Pulsed	255	А			
PD	Total Dissipation @Tc=25°C	500	W			
Tj	Max. Operating Junction Temperature	150	°C			
T <sub>stg</sub>	Storage Temperature	-55~150	°C			

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(j-c)	Channel-to-case thermal resistance	0.25	°C/W
Rth(j-a)	Channel-to-ambient thermal resistance	62	°C/W









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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =1mA	650			V
$V_{GS(th)}$	Gate Threshold Voltage	VDS=VGS; ID=3.3mA	3.5		4.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =33.1A			41	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = 20V; VDS=0V			0.1	mA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =650V; V <sub>GS</sub> = 0V			3.5	μ <b>Α</b>
Vsd	Diode forward voltage	I <sub>F</sub> =49.6A, V <sub>GS</sub> = 0V				V

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